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APPLICATION NO	LICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/712,086	10/712,086 11/13/2003		Kazuhisa Yamamoto	YAO-3750US2	7925		
23122	7590	09/28/2005		EXAM	EXAMINER		
RATNER	PRESTL	A		RODGERS, COLLEEN E			
POBOX		PA 19482-0980		ART UNIT	PAPER NUMBER		
VALLET	FORGE,	FA 19402-0900		2813	· <u>·</u>		
				DATE MAILED: 09/28/2005			

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application	No.	Applicant(s)				
Office Action Summary		10/712,086		YAMAMOTO ET AL.				
		Examiner		Art Unit				
		Colleen E. F	Rodgers	2813	62			
The MAILING DATE of this c Period for Reply	ommunication app	ears on the	cover sheet with the c	orrespondence ad	Idress			
A SHORTENED STATUTORY PER THE MAILING DATE OF THIS CO - Extensions of time may be available under the after SIX (6) MONTHS from the mailing date of - If the period for reply specified above is less the - If NO period for reply is specified above, the mailing to reply within the set or extended perion Any reply received by the Office later than three earned patent term adjustment. See 37 CFR 1	MMUNICATION. provisions of 37 CFR 1.13 this communication. an thirty (30) days, a reply aximum statutory period w d for reply will, by statute, e months after the mailing	36(a). In no even within the statuto vill apply and will cause the applic	t, however, may a reply be tim bry minimum of thirty (30) days expire SIX (6) MONTHS from ation to become ABANDONE	nely filed s will be considered timel the mailing date of this c D (35 U.S.C. § 133).	ly. commu <mark>nication.</mark>			
Status	•		·					
 1) Responsive to communication 2a) This action is FINAL. 3) Since this application is in concluded in accordance with the 	2b)⊠ This ndition for allowan	action is no nce except fo	n-final. or formal matters, pro		e merits is			
Disposition of Claims	•	ŕ						
4)⊠ Claim(s) <u>78-83</u> is/are pending 4a) Of the above claim(s) 5)□ Claim(s) is/are allowe 6)⊠ Claim(s) <u>78 and 82</u> is/are reju 7)⊠ Claim(s) <u>79-81 and 83</u> is/are 8)□ Claim(s) are subject to	is/are withdrawd. cted. objected to.	vn from con:						
Application Papers								
9) The specification is objected to 10) The drawing(s) filed on Applicant may not request that a Replacement drawing sheet(s) if 11) The oath or declaration is object.	is/are: a) acce any objection to the oncluding the correcti	epted or b) drawing(s) be ion is required	held in abeyance. See	e 37 CFR 1.85(a). jected to. See 37 Cl				
Priority under 35 U.S.C. § 119								
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 								
Attachment(s)								
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing F Information Disclosure Statement(s) (PTO Paper No(s)/Mail Date 11/13/2003 			I) Interview Summary Paper No(s)/Mail Da Notice of Informal P Other:	ate	O-152)			

Application/Control Number: 10/712,086

Art Unit: 2813

DETAILED ACTION

1. This Office Action responds to the communication of 18 November 2004. The Notice of Non-Compliant Amendment of 4 June 2004 under 37 CFR 1.121 is hereby vacated.

Claim Rejections - 35 USC § 102

72. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 3. Claims 78 is rejected under 35 U.S.C. 102(b) as being anticipated by Mizuuchi et al (USPN 5,323,262).

Regarding claim 78, Mizuuchi et al discloses a method for producing an optical element, comprising: a step of forming a proton exchange layer in an LiNb_xTa_{1-x}O₃ ($0 \le X \le 1$) substrate [see the Abstract, where X = 0]; a high-temperature annealing step of performing a heat treatment for the substrate at a temperature of 150°C or higher [see col. 5, lines 37-39 and col. 9, lines 61-64, where the Curie temperature is given as 604°C]; and a low-temperature annealing step of performing a heat treatment for the substrate at a temperature of 120°C or lower for 1 hour or more [see col. 3, lines 40-41] so as to mitigate strain introduced in the proton exchange layer by the high temperature annealing step. The limitation "so as to mitigate strain introduced in the proton exchange layer by the high temperature annealing step" is merely an intended use and is not granted patentable weight.

4. Claim 82 is rejected under 35 U.S.C. 102(b) as being anticipated by Yamamoto et al (USPN 5,253,259).

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Yamamoto et al discloses a method for producing an optical element, comprising: a step of performing a proton-exchange process for an LiNb_xTa_{1-x}O₃ ($0 \le X \le 1$) substrate [see col. 5, lines 51-56]; a first annealing step of performing a first heat treatment for the substrate at a first temperature, after performing the proton exchange process [see col. 1, lines 61-65]; and a second annealing step of performing a second heat treatment for a substrate at a second temperature, after performing the first heat treatment [see col. 1, lines 65-68; col. 5, lines 49-51], wherein the second temperature is lower than the first temperature by 200°C or more. The first process step cited above occurs at about 1100°C and the second occurs at 350°C, which results in a temperature differential of 750°C.

5. Claim 82 is rejected under 35 U.S.C. 102(b) as being anticipated by Nutt et al, "Simple control of Ti-diffused LiNbO₃ waveguide profile and propagation characteristics," *Electronics Letters*, Vol. 24, No. 1, 7 January 1988, p. 56-58.

Nutt et al discloses a method for producing an optical element, comprising: a step of performing a proton-exchange process for an LiNb_xTa_{1-x}O₃ ($0 \le X \le 1$) substrate [see paragraph bridging pages 56 and 57]; a first annealing step of performing a first heat treatment for the substrate at a first temperature, after performing the proton exchange process [see paragraph bridging pages 56 and 57]; and a second annealing step of performing a second heat treatment for a substrate at a second temperature, after performing the first heat treatment [see paragraph bridging pages 56 and 57], wherein the second temperature is lower than the first temperature by 200°C or more. The first process step cited above occurs at about 1000°C and the second occurs at 210°C, which results in a temperature differential of 790°C.

Allowable Subject Matter

6. Claims 79-81 and 83 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Colleen E. Rodgers whose telephone number is (571) 272-0237. The examiner can normally be reached on Monday through Friday, 7:30 AM to 4:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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